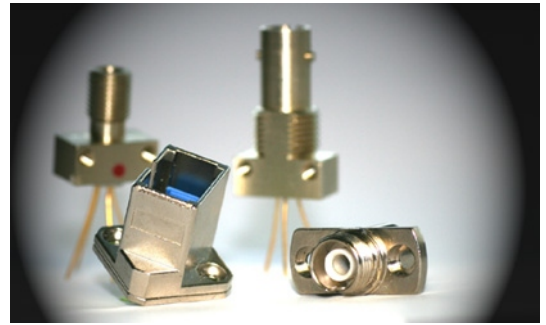


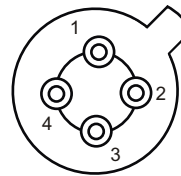
PIN-TIA Receiver 622 Mbps with AGC

Features of Diode

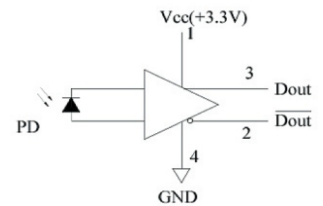
- InGaAs/InP PIN Photodiode with Transimpedance Amplifier
- High sensitivity with AGC
- Differential ended output
- Single supply voltage 3.3 V
- -40 to 85 °C operating temperature
- Integrated 4-pin TO-46 ball lens cap package
- 622 Mbps SONET/SDH/ATM receivers
- Bi-Directional optical module/transceiver



PINOUT



Bottom view



Functional Schematic

Absolute maximum ratings

Parameter	Min.	Max.
Storage temperature	-40 °C	85 °C
Operating temperature	-40 °C	85 °C
Supply voltage		4 V

Number	Function
1	V _{CC}
2	D _{out}
3	D _{out}
4	GND

Electrical-optical characteristics

Parameter Laser Diode	Test Condition	Min.	Typ.	Max.
Power supply	T _c = 25 °C	3.0 V	3.3 V	3.6 V
Differential output voltage	T _c = 25 °C			0.4 V
Supply current	T _c = 25 °C		20 mA	26 mA
Detection range	T _c = 25 °C	1100 nm	1310 nm	1650 nm
Gain @ 10 Mbps Differential	Measure diff. AC coupled, RL=50	13 V/mW	16.5 V/mW	21 V/mW
Bandwidth	T _c = 25 °C	435 MHz	580 MHz	
Saturation power	BER < 10 ⁻¹⁰ @ 622 Mbps, Er = 10 dB	-3 dBm	0 dBm	
Sensitivity	BER < 10 ⁻¹⁰ @ 622 Mbps, Er = 10 dB		-32 dBm	-29 dBm
Output resistance	T _c = 25 °C	60	75	90
Possible receptacle (type A)	ST1, ST2, ST4, P2, LC, SC, FC1, FC2, Fiberdip, SMA1, SMA2			

Compliant with RoHS-requirements (2002/95/EG vom 27.01.2003)

Note: The above product specifications are subject to change without notice.